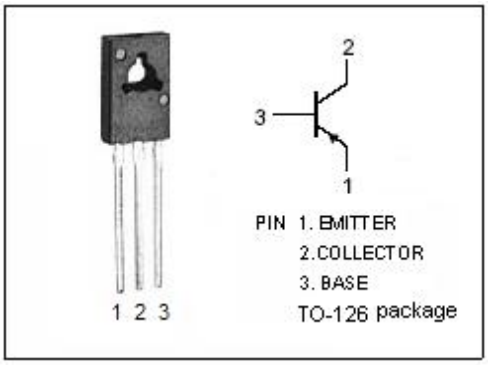
isc Silicon PNP Power Transistors — 2SA1220/A

DESCRIPTION

- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -120V(Min)-2SA1220
  = -160V(Min)-2SA1220A
- Complement to Type 2SC2690/A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

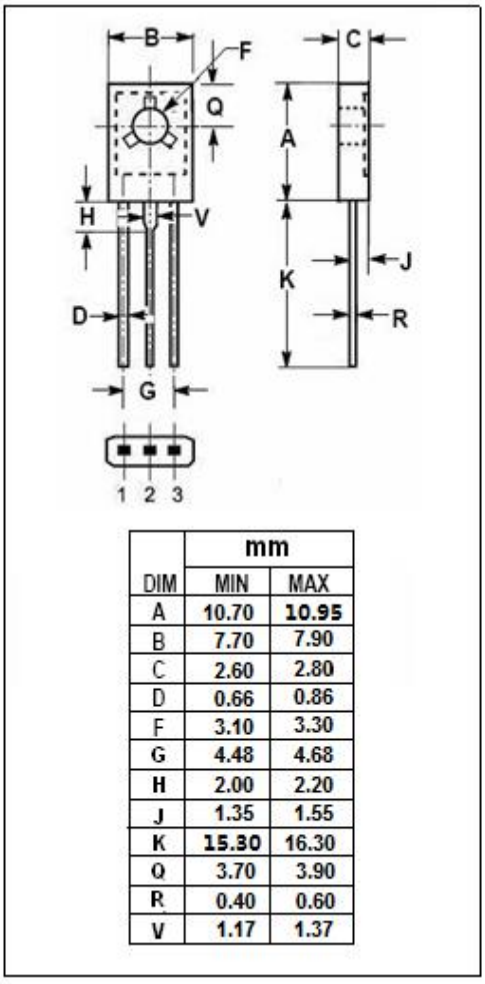
APPLICATIONS

- Adudio frequency power amplifier
- High frequency power amplifier



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CBO}	Collector-Base Voltage	2SA1220	-120	V
		2SA1220A	-160	
V_{CEO}	Collector-Emitter Voltage	2SA1220	-120	V
		2SA1220A	-160	
V_{EBO}	Emitter-Base Voltage		-5	V
I_C	Collector Current-Continuous		-1.2	A
I_{CM}	Collector Current-Peak		-2.5	A
I_B	Base Current-Continuous		-0.3	A
P_C	Collector Power Dissipation @ T_a=25℃		1.2	W
	Total Power Dissipation @ T_C=25℃		20	
T_J	Junction Temperature		150	℃
T_{stg}	Storage Temperature Range		-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1A; I_B= -0.2A			-0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1A; I_B= -0.2A			-1.3	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C=0			-1.0	μA
h_{FE-1}	DC Current Gain	I_C= -5mA ; V_{CE}= -5V	35			
h_{FE-2}	DC Current Gain	I_C= -0.3A ; V_{CE}= -5V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C= -0.2A ; V_{CE}= -5V		175		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V;f_{test}= 1.0MHz		26		pF

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320